#### Electron charge qubits on solid neon with 0.1 millisecond coherence time

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# Theory/proposal and related work

- Idea is to remove "solid state qubit" from noisy crystal. (Similar idea exists for superfluid Helium)
- Proposal/theory paper on spin-qubit on solid Ne: <a href="https://arxiv.org/pdf/2205.00589.pdf">https://arxiv.org/pdf/2205.00589.pdf</a>

Metric	T <sub>1</sub>	T <sub>2</sub> *	T <sub>2</sub> echo
Natural Ne (2700ppm <sup>21</sup> Ne)	Long (not specified)	0.16 ms	30ms
purified Ne (1000ppm <sup>21</sup> Ne)	Long (not specified)	0.43 ms	81s

• Related work: Electrons on superfluid LHe (probably same device but different "filling")



# <u>Device</u>



#### "Fabrication":

- Make chip with Nb gates/resonator on Si in "normal" fabrication
- Cool down in pressure cell with self-made regulator ("gas-handling puff system")
- Walk through phase diagram to form best possible solid Ne in cooldown
- Electron(s) gets emitted from a tungsten filament and placed onto surface

From electron on LHe paper







Position across channel y (µm)

## Solid Neon



- 1. Fill controlled amount of Ne in cell at 26K to wet the chip
- 2. Cool down along liquid-gas coexisting line
- 3. Keep going across Triple Point at 24.6K (0.43bar) to turn into solid
- 4. "anneal" at 10K for 1-2h
- 5. Cool to base (10mK)
- 6. Final state: Estimate ~10s nm of Neon on top of chip

## Standard cQED measurements



#### **Experiments:**

- Change qubit frequency with left vs right guard voltage  $\Delta V_{rg}$
- Bring on resonance and see anticrossing (c,d)
  -> extract g and losses (κ + γ)
- Fix resonator and drive qubit with second tone
  -> find charge qubit sweetspot vs detuning (e)
- Cuts across sweetspot with varying drive power show Stark-shift
  -> Find single photon limit (d)

#### Extracted numbers\*:

fr=6.4262 GHz,  $\kappa/2\pi$  = 0.46 MHz, g/2 $\pi$ =2.3MHz,  $\gamma/2\pi$ =0.36MHz



### Single qubit: Dispersive shift and Rabi



- Drive qubit using Gaussian drive tone
- On sweet spot!
- See dispersive shift (Fig c,d)
- Measure Rabi: T<sub>rabi</sub>=80µs
- Dispersive shift:  $\chi/2\pi$ =-0.13MHz

## Single qubit: On/off sweetspot



# Single qubit: CPMG and fidelities

Important note: This is in another configuration using "another electron"



- In previous setting they were limited by Purcell-type decay for read-out (T<sub>1</sub> limit)
- In new potential the resonator is further from the qubit frequency at the sweetspot (-270MHz vs -34.7MHz)
- Here  $T_1 = 88.4 \mu s$ ,  $T_2^* = 3.9 \mu s$  which makes it a worse qubit but better for read-out.
- Do CPMG and recover most of previous level of  $T_2^{echo}$  with 80 CPMG pulses
- Read out fidelity (without SC amplifiers) 97.5%
- Randomized benchmarking: Gate fidelity 99.95%



Wigner-molecule might be a bit different...

## Coupling two electrons to the resonator



ΔVr : "(offset) resonator voltage" Is that the offset compared to trap?

 $\Delta Vrg:$  Resonator guard bias



- Two electrons in same trap (where is not clear)
- Tune with resonator offset voltage  $\Delta V_r$  and trap guard voltage  $\Delta V_{rg}$
- Results matched with input-output theory
- g<sub>1</sub>/2π=3.6MHz, g<sub>2</sub>/2π=1.8MHz, γ<sub>1</sub>/2π=1.5MHz, γ<sub>2</sub>/2π=1.6MHz